

# MPFF200R12RB 1200V 200A IGBT Module

## **Electrical Features**

- Trench/Fieldstop IGBT
- Low VCE(sat)
- VCE(sat) with positive temperature coefficient
- $10 \ \mu$  s short circuit capability
- Fast&soft reverse recovery anti-parallel FWD
- Low inductance case



## **Typical Applications**

- Motor Drives
- High Power Converters
- UPS System

IGBT,	Inverter

Maximu	m Rated Values						
Symbol	Item	Conditions			Rating		Unit
IGBT		·					
V <sub>CES</sub>	Collector-emitter voltage	T <sub>vj</sub> =25°C			1200V		V
V <sub>GES</sub>	Gate-emitter voltage	-			±20		V
Ic	Collector current,DC	T <sub>C</sub> =100°C,T <sub>vj</sub> =175°	°C		200		A
ICRM	Repetitive peak collector current	t <sub>p</sub> =1ms			40	00	A
t <sub>SC</sub>	Short circuit withstand time	$V_{GE}=15V, V_{CC}=600V, T_{vj}\leq 150^{\circ}C$			10		us
Ptot	Total power dissipation	$T_{C}=25^{\circ}C, T_{vj}=175^{\circ}C$			1071		W
Charact	eristics Values						
Symbol	Item	Conditions			Values		Unit
IGBT		·		Min.	Тур.	Max.	
ICES	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0$	V <sub>CE</sub> =1200V,V <sub>GE</sub> =0V,T <sub>vj</sub> =25°C		-	1	mA
I <sub>GES</sub>	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{CE}=20V, T_{CE$	V <sub>CE</sub> =0V,V <sub>GE</sub> =20V,T <sub>vj</sub> =25°C		-	250	nA
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	$I_{C}=7.4\text{mA}, V_{CE}=V_{GI}$	$I_C = 7.4 \text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		6.0	7.0	
	Collector-emitter saturation voltage	I _200 A	T <sub>vj</sub> =25°C	-	1.97	2.3	v
V <sub>CEsat</sub> C		I <sub>C</sub> =200A V <sub>GE</sub> =15V	T <sub>vj</sub> =125°C	-	2.26	-	
			T <sub>vj</sub> =150°C	-	2.3	-	
Cies	Input capacitance	V <sub>CE</sub> =25V,V <sub>GE</sub> =0V		-	14.1	-	E
Cres	Reverse transfer capacitance	f=1MHz,T <sub>vj</sub> =25°C		-	0.48	-	nF
Q <sub>G</sub>	Gate charge	V <sub>CC</sub> =600V, I <sub>C</sub> =200A, V <sub>GE</sub> =15V		-	803	-	uC
Rg	Internal gate resistance	T <sub>vj</sub> =25°C			0.84		Ω

			_				-
		T <sub>vj</sub> =25°C	-	169.6	-	_	
t <sub>d(on)</sub>	t <sub>d(on)</sub> Turn-on delay time		T <sub>vj</sub> =125°C	-	156.8	-	_
			T <sub>vj</sub> =150°C	-	158.4	-	
			T <sub>vj</sub> =25°C	-	110.4	-	
t <sub>r</sub>	Rise time		T <sub>vj</sub> =125°C	-	113.6	-	
			T <sub>vj</sub> =150°C	-	110.4	-	
		V <sub>CC</sub> =600V,	T <sub>vj</sub> =25°C	-	392.0	-	ns
$t_{d(off)}$	Turn-off delay time	Ic=200A,	T <sub>vj</sub> =125°C	-	444.8	-	
		$V_{GE}=\pm 15V$ ,	T <sub>vj</sub> =150°C	-	491.2	-	
	t <sub>f</sub> Fall time	$R_{G(on)}=10 \Omega$ ,	T <sub>vj</sub> =25°C	-	219.2	-	
$t_{\mathrm{f}}$		$R_{G(off)}=10 \Omega$ ,	T <sub>vj</sub> =125°C	-	291.2	-	1
		Lload=200uH	T <sub>vj</sub> =150°C	-	307.2	-	
		T <sub>vj</sub> =25°C	-	22.7	-		
Eon	Turn-on energy (per pulse)		T <sub>vj</sub> =125°C	-	30.3	-	
			T <sub>vj</sub> =150°C	-	33.1	-	- -
			T <sub>vi</sub> =25°C	-	17.1	_	mJ
E <sub>off</sub>	Turn-off energy (per pulse)		T <sub>vi</sub> =125°C	-	21.4	-	-
			T <sub>vj</sub> =150°C	-	22.5	-	-
R <sub>thJC</sub>	Thermal resistance, junction to case	per IGBT	J	-	_	0.14	K/W
RthCH	Thermalresistance, case to heatsink	per IGBT/ λgrease	=1W/(m·K)	-	0.04	-	K/W
	Temperature under switching			40		150	°C
$T_{vjop}$	conditions			-40		150	
Diode,	Inverter						
Maximu	m Rated Values						
Symbol	Item	Co	nditions		Rat	ing	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	T <sub>vj</sub> =25°C			12	00	V
$\mathbf{I}_{\mathrm{F}}$	Forward current,DC	$T_{C}=100^{\circ}C, T_{vj}=150$	٥°C		10	00	A
I <sub>FRM</sub>	Repetitive peak forward current	t <sub>p</sub> =1ms				200	
Charact	eristic Values						
		L 100 A	T <sub>vj</sub> =25°C	-	1.67	-	
$V_{\rm F}$	Continuous forward voltage	$I_F=100A$	T <sub>vj</sub> =125°C	-	1.51	-	V
		V <sub>GE</sub> =0V	T <sub>vj</sub> =150°C	-	1.45	-	
			T <sub>vj</sub> =25°C	-	-	-	
I <sub>RM</sub>	Peak reverse recovery current		T <sub>vj</sub> =125°C	-	119.0	-	A
			T <sub>vj</sub> =150°C	-	132.5	-	-
		_	T <sub>vj</sub> =25°C	-	_	-	
t <sub>rr</sub>	t <sub>rr</sub> Reverse recovery time	V <sub>R</sub> =600V	T <sub>vj</sub> =125°C	_	459.2	_	ns
	$I_F=100A$	T <sub>vj</sub> =150°C	_	484.0	_	-	
	$di_{\rm F}/dt=-1400 {\rm A/\mu s}$	$T_{vj}=25^{\circ}C$	-	_	_		
Qr	Q <sub>r</sub> Repetitive peak forward current		$T_{vj}=125^{\circ}C$	-	23.3	-	μC
		T <sub>vj</sub> =150°C	-	28.3	_		
		-	$T_{vj} = 150 \text{ C}$ $T_{vj} = 25^{\circ}\text{C}$	-		-	
F	E <sub>rec</sub> Recovered charge		$T_{vj}=23$ C $T_{vj}=125$ °C	-	8.83	-	mJ
Lrec			$T_{vj}=123$ C $T_{vj}=150$ °C		10.55	-	- 1115
			1 <sub>vj</sub> -150 C	-	10.33	-	

# MPFF200R12RB

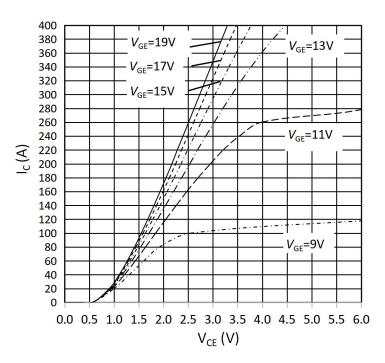
R <sub>thJC</sub>	Thermal resistance, junction to case	per diode	-	-	0.27	K/W
R <sub>thCH</sub>	Thermalresistance, case to heatsink	per IGBT/ $\lambda$ grease=1W/(m·K)	-	0.04	-	K/W
T <sub>vjop</sub>	Temperature under switching conditions		-40		150	°C

## Module

Symbol	Item	Conditions	Rating		Unit	
VISOL	Isolation voltage	Terminals to baseplate, RMS,f=50Hz,t=1min	2500		V	
-	Material of module baseplate	-	Cu		-	
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al <sub>2</sub> O <sub>3</sub>			-
T <sub>stg</sub>	Storage temperature	-	-40~125		5	°C
Symbol	Item	Canditions	Values			Unit
		Conditions		Тур.	Max.	
М	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	23	-	
		Terminal to base plate	-	29	-	mm
da	Clearance	Terminal to terminal	-	11	-	
		Terminal to base plate	-	23	-	mm
m	Weight	-	-	150	-	g

output characteristic IGBT, Inverter (typical)

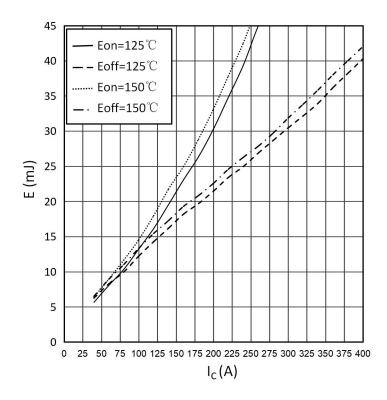
 $I_{C} = f(V_{CE})$  $V_{GE} = 15 V$ 





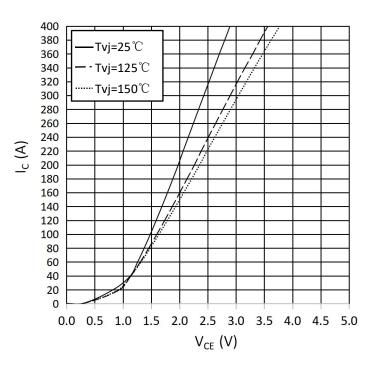
 $E_{on} = f(I_C), E_{off} = f(I_C)$ 

 $V_{GE} = \pm 15 V, R_{Gon} = 10 \Omega, R_{Goff} = 10 \Omega, V_{CE} = 600 V$ 



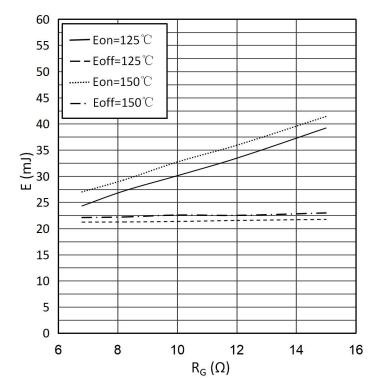
## output characteristic IGBT, Inverter (typical)

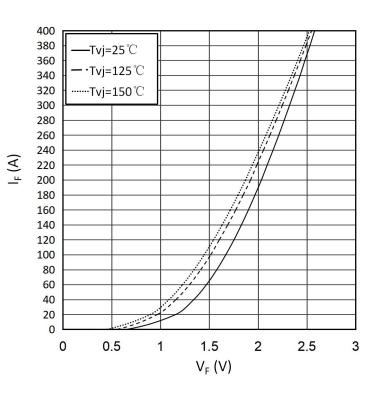
 $I_{C} = f(V_{CE})$  $T_{vj} = 150^{\circ}C$ 



#### switching losses IGBT, Inverter(typical)

 $E_{on} = f(R_G), E_{off} = f(R_G)$  $V_{GE} = \pm 15V, I_C = 200A, V_{CE} = 600V$ 

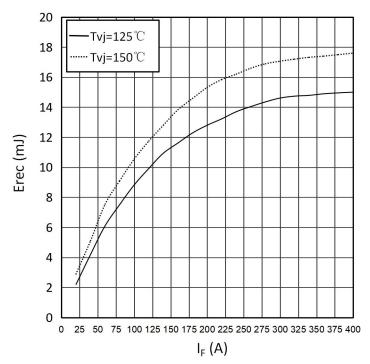




# forward characteristic of Diode, Inverter (typical) $I_F = f\left(V_F\right)$

switching losses Diode, Inverter (typical)

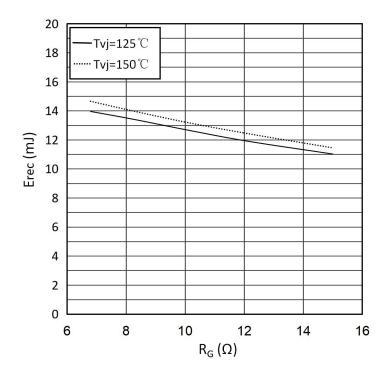
$$\begin{split} E_{rec} &= f\left(I_{F}\right) \\ R_{Gon} &= 10\Omega, \, V_{CE} &= 600V \end{split}$$



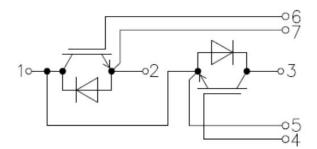
switching losses Diode, Inverter (typical)

 $E_{rec} = f(R_G)$ 

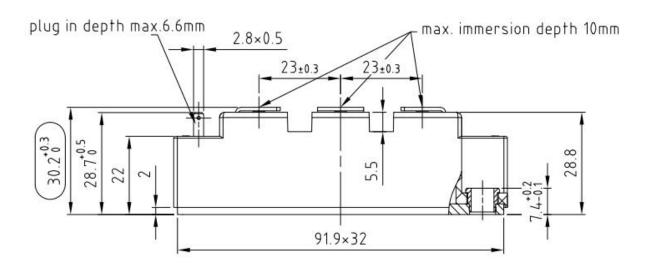
 $I_F=200A, V_{CE}=600V$ 

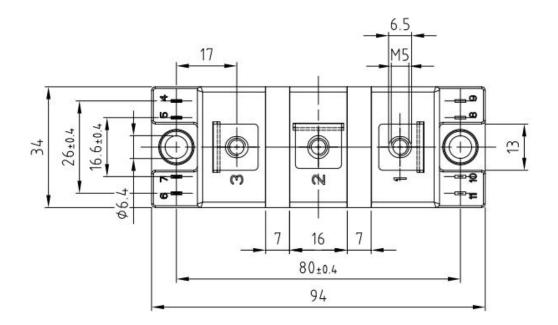


## Circuit diagram headline



# Package outlines (Unit: mm)





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